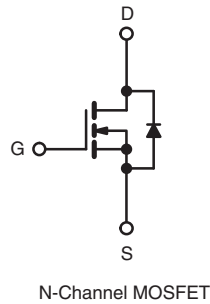
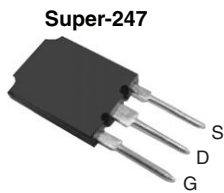


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.087
Q_g (Max.) (nC)	380	
Q_{gs} (nC)	80	
Q_{gd} (nC)	190	
Configuration	Single	



FEATURES

- Superfast Body Diode Eliminates the Need for External Diodes in ZVS Applications
- Lower Gate Charge Results in Simpler Drive Requirements
- Enhanced dV/dt Capabilities Offer Improved Ruggedness
- Higher Gate Voltage Threshold Offers Improved Noise Immunity
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT

APPLICATIONS

- Zero Voltage Switching SMPS
- Telecom and Server Power Supplies
- Uninterruptible Power Supplies
- Motor Control Applications

ORDERING INFORMATION	
Package	Super-247
Lead (Pb)-free	IRFPS40N50LPbF
	SiHFPS40N50L-E3
SnPb	IRFPS40N50L
	SiHFPS40N50L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	500	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25^\circ\text{C}$	A	
		$T_C = 100^\circ\text{C}$		
Pulsed Drain Current ^a	I_{DM}	180		
Linear Derating Factor		4.3	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy ^b	E_{AS}	920	mJ	
Repetitive Avalanche Current ^a	I_{AR}	46	A	
Repetitive Avalanche Energy ^a	E_{AR}	54	mJ	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	540	W
Peak Diode Recovery dV/dt^c		dV/dt	34	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		

Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25^\circ\text{C}$, $L = 0.86$ mH, $R_g = 25 \Omega$, $I_{AS} = 46$ A (see fig. 12).
- $I_{SD} \leq 46$ A, $di/dt \leq 550$ A/ μs , $V_{DD} \leq V_{DS}$, $T_J \leq 150^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient ^a	R_{thJA}	-	40	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.24	-	
Maximum Junction-to-Case (Drain) ^a	R_{thJC}	-	0.23	

Note

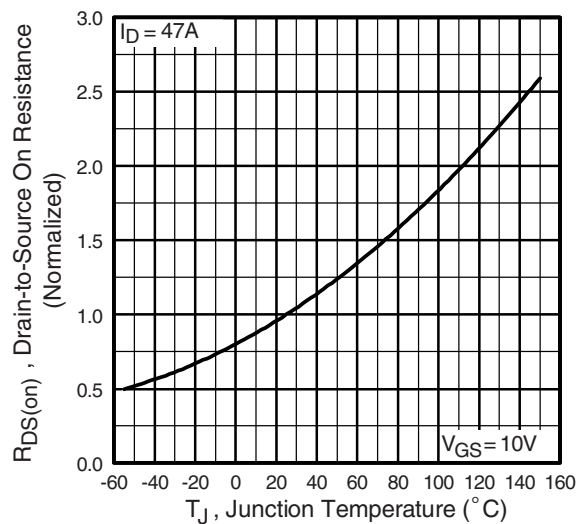
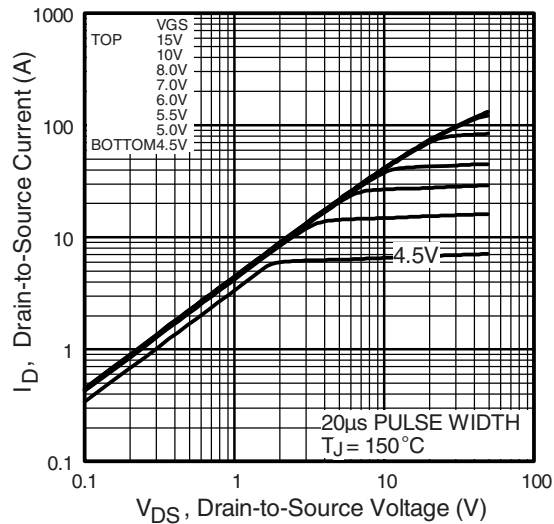
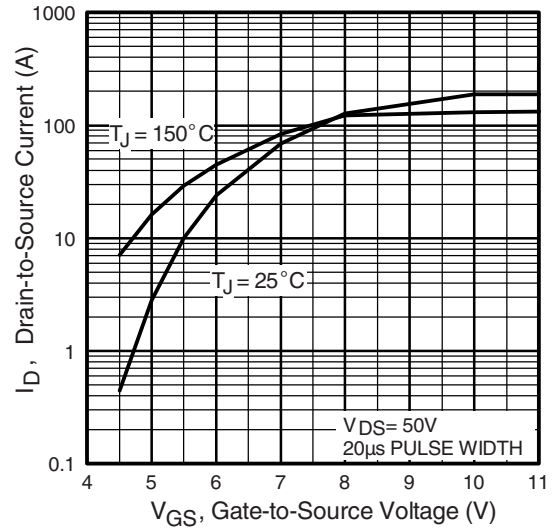
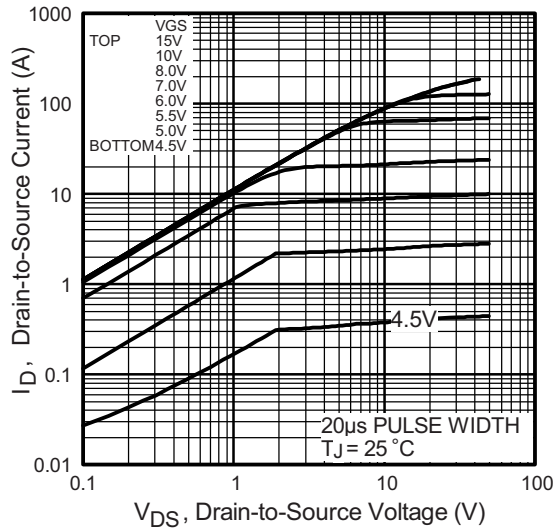
a. R_{th} is measured at T_J approximately 90 °C.

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	500	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, $I_D = 1\text{ mA}$	-	0.60	-	V/°C	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.0	-	5.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	50	μA	
		$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ °C}$	-	-	2.0	mA	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 28\text{ A}^b$	-	0.087	0.100	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 46\text{ A}$	21	-	-	S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	8110	-	pF	
Output Capacitance	C_{oss}		-	960	-		
Reverse Transfer Capacitance	C_{rss}		-	130	-		
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}$, $f = 1.0\text{ MHz}$	-	11200	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 400\text{ V}$, $f = 1.0\text{ MHz}$	-	240	-	
Effective Output Capacitance (Energy Related)	$C_{oss\text{ eff. (ER)}}$	$V_{DS} = 0\text{ V to }400\text{ V}^c$	-	310	-		
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 46\text{ A}$, $V_{DS} = 400\text{ V}$, see fig. 7 and 15 ^b	-	-	380	nC
Gate-Source Charge	Q_{gs}			-	-	80	
Gate-Drain Charge	Q_{gd}			-	-	190	
Internal Gate Resistance	R_G	$f = 1\text{ MHz}$, open drain		-	0.90	-	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}$, $I_D = 46\text{ A}$, $R_G = 0.85\text{ }\Omega$, $V_{GS} = 10\text{ V}$, see fig. 14a and 14b ^b	-	27	-	ns	
Rise Time	t_r		-	170	-		
Turn-Off Delay Time	$t_{d(off)}$		-	50	-		
Fall Time	t_f		-	69	-		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode	-	-	46	A	
Pulsed Diode Forward Current ^a	I_{SM}		-	-	180		
Body Diode Voltage	V_{SD}	$T_J = 25\text{ °C}$, $I_S = 46\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	1.5	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ °C}$, $I_F = 46\text{ A}$	-	170	250	ns	
		$T_J = 125\text{ °C}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	220	330		
Body Diode Reverse Recovery Charge	Q_{rr}	$T_J = 25\text{ °C}$, $I_S = 46\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	705	1060	nC	
		$T_J = 125\text{ °C}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$	-	1.3	2.0		
Reverse Recovery Current	I_{RRM}	$T_J = 25\text{ °C}$	-	9.0	-	A	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 400\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
 $C_{oss\text{ eff. (ER)}}$ is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



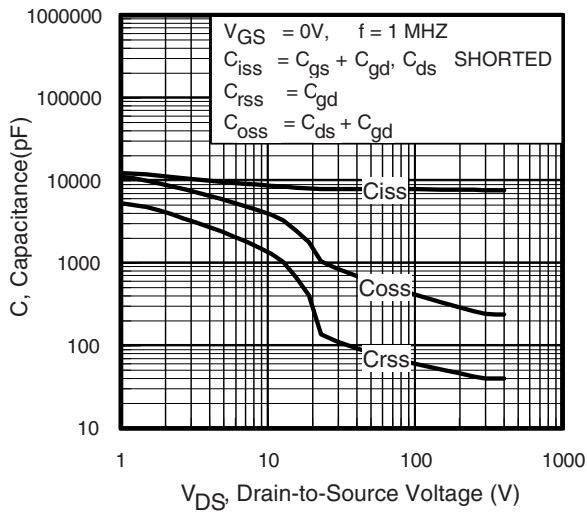


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

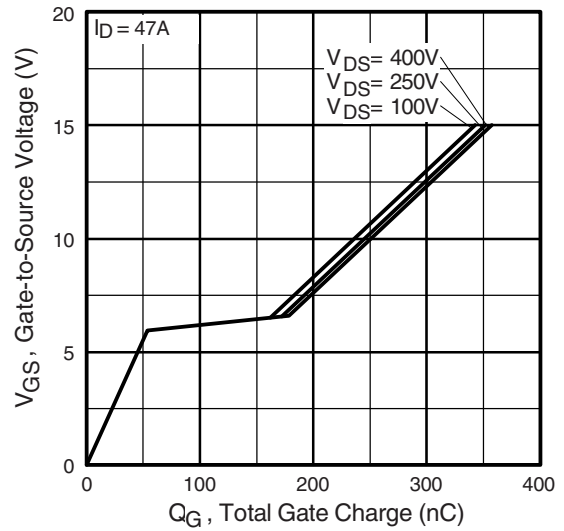


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

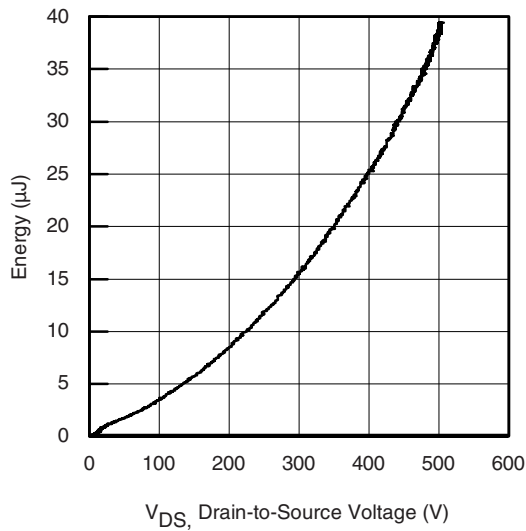


Fig. 6 - Typical Output Capacitance Stored Energy vs. V_{DS}

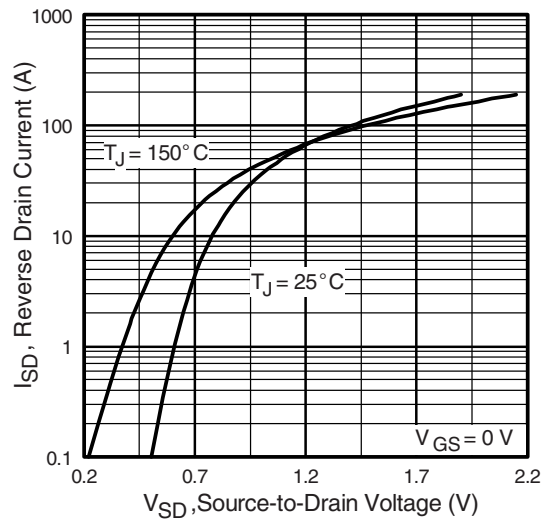


Fig. 8 - Typical Source Drain Diode Forward Voltage

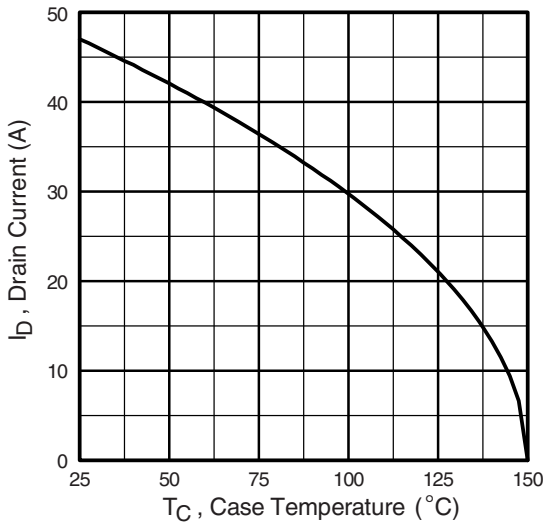


Fig. 9 - Maximum Drain Current vs. Case Temperature

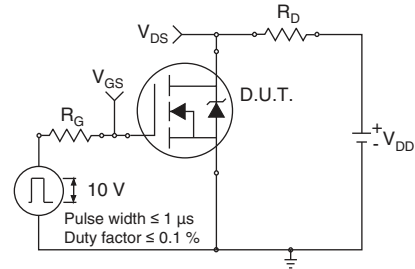


Fig. 10a - Switching Time Test Circuit

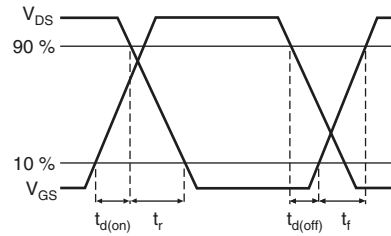


Fig. 10b - Switching Time Waveforms

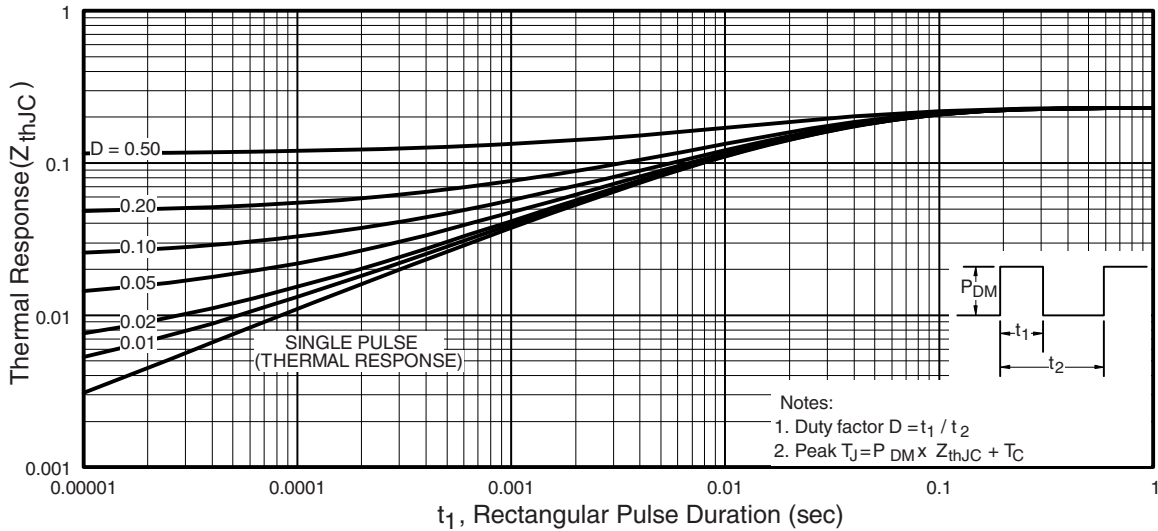


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

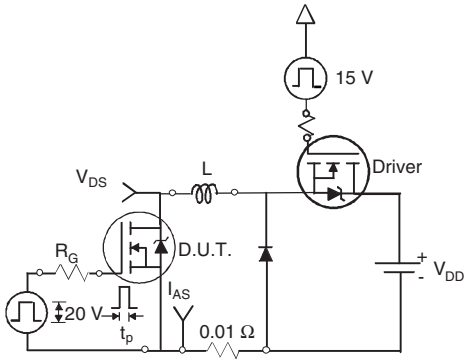


Fig. 12a - Unclamped Inductive Test Circuit

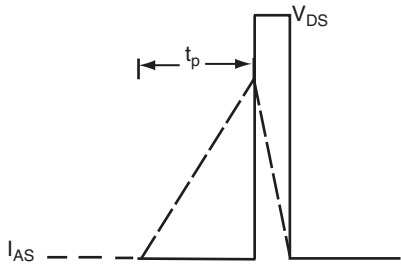


Fig. 12b - Unclamped Inductive Waveforms

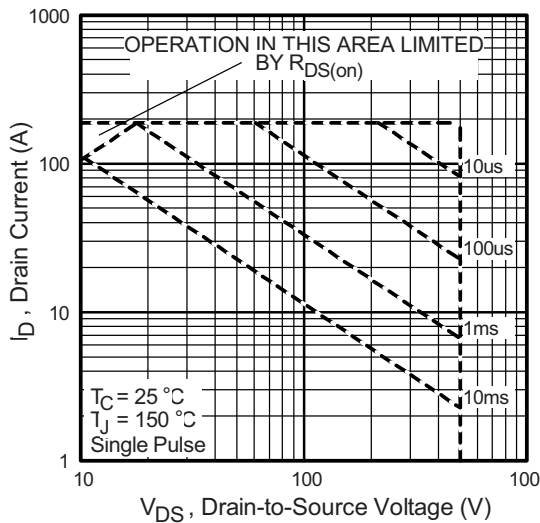


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

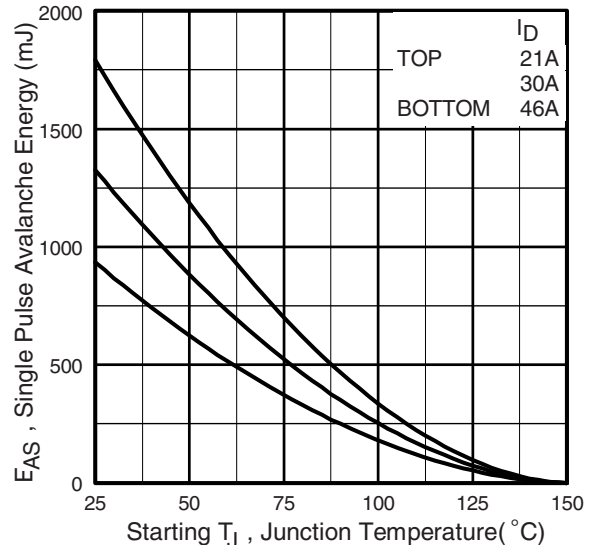


Fig. 12d - Maximum Safe Operating Area

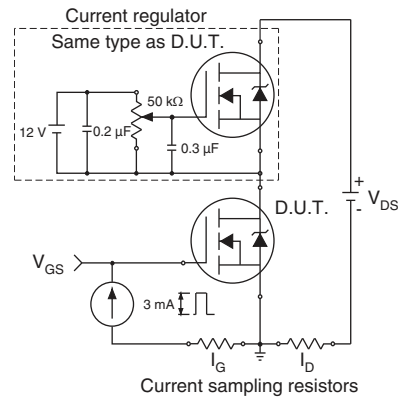


Fig. 13a - Gate Charge Test Circuit

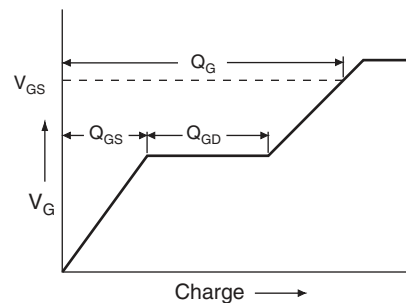
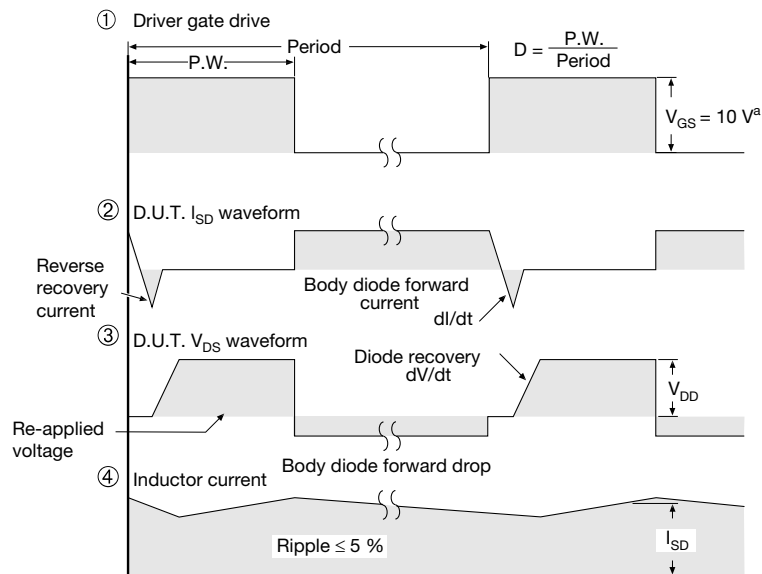
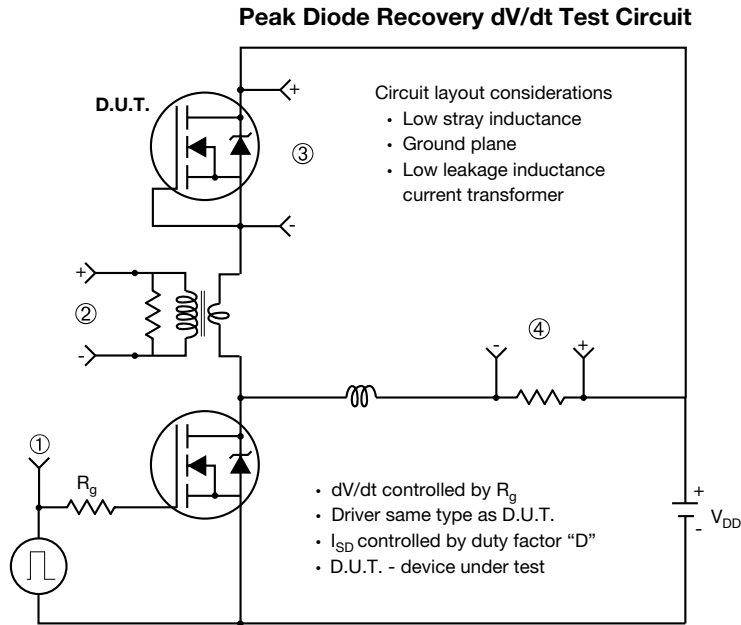


Fig. 13b - Basic Gate Charge Waveform

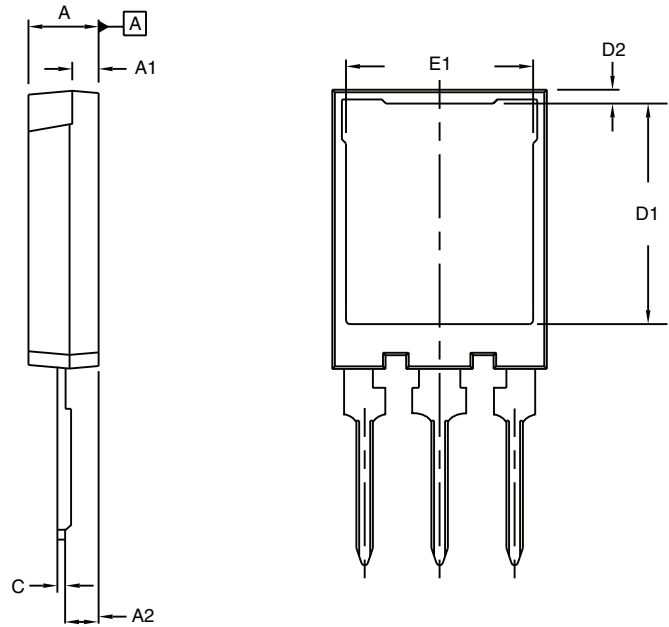
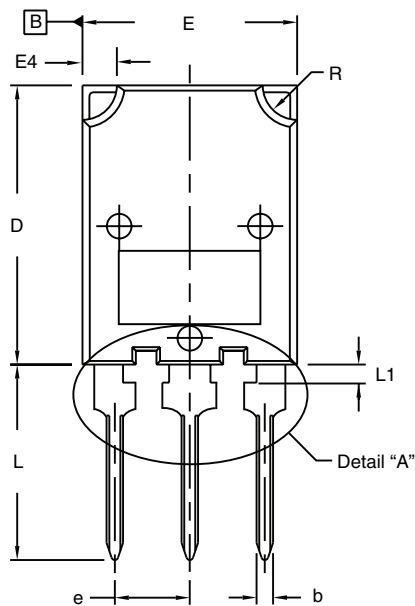


Note
 a. $V_{GS} = 5 V$ for logic level devices

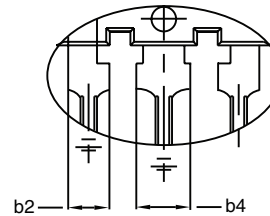
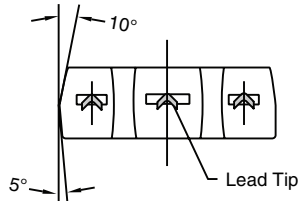
Fig. 14 - For N-Channel

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TO-274AA (HIGH VOLTAGE)



⊕ 0.10 (0.25) ⊕ B A ⊕



Detail "A"
Scale: 2:1

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c	0.80	1.20	0.031	0.047
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

ECN: S-82247-Rev. A, 06-Oct-08
DWG: 5975

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body.
3. Outline conforms to JEDEC outline to TO-274AA.



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